

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI TVU005** is a Common Emitter Device Designed for High Linearity Class A Television Band IV and V Transmitters.

**FEATURES INCLUDE:**

- Gold Metalization
- Emitter Ballasting

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	500 mA
<b>V<sub>CB</sub></b>	45 V
<b>P<sub>DISS</sub></b>	8.0 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-55 °C to +200 °C
<b>T<sub>STG</sub></b>	-55 °C to +200 °C
<b>q<sub>JC</sub></b>	22.0 °C/W

**PACKAGE STYLE .280 4L STUD**

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25.65	1.055/26.80
B	.220/5.59	.230/5.84
C	.270/6.86	.285/7.24
D	.003/0.08	.007/0.18
E	.117/2.97	.137/3.48
F	.5/2/14.53	
G	.130/3.30	
H	.275/6.99	.285/7.24
I	6.40/16.26	
J	.175/4.45	.21/75.51

1 = COLLECTOR    2 = BASE  
3 & 4 = EMITTER

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 20 mA	24			<b>V</b>
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 1.0 mA	45			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1.0 mA	3.5			<b>V</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V    I <sub>C</sub> = 100 mA	20		120	<b>---</b>
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 28 V    f = 1.0 MHz		5.0		<b>pF</b>
<b>P<sub>G</sub> IMD<sub>3</sub></b>	V <sub>CE</sub> = 20 V    I <sub>C</sub> = 220 mA    Pref = 0.5 W VISION CARRIER = -8.0 dB    f = 860 MHz SOUND CARRIER = -7.0 dB    CHROMA = -16 dB	10	11	-58	<b>dB</b>